



Features

- Hall based differential speed sensor
- High magnetic sensitivity
- · Large operating airgap
- Dynamic self-calibration principle
- Adaptive hysteresis
- · Output protocols with and without direction of rotation detection
- · High vibration suppression capabilities
- Three wire voltage interface
- Magnetic encoder and ferromagnetic wheel application
- · High immunity against ESD, EMC and mechanical stress, improved voltage dropout capability
- · Automotive operating temperature range
- End-of-line programmable to adjust transmission requirements.
- Green Product (RoHS compliant)
- AEC Qualified

Applications

The TLE4959C FX is an integrated differential Hall speed sensor ideally suited for transmission applications. Its basic function is to provide information about rotational speed and direction of rotation to the transmission control unit. TLE4959C FX includes a sophisticated algorithm which actively suppresses vibration while keeping excellent airgap performance.

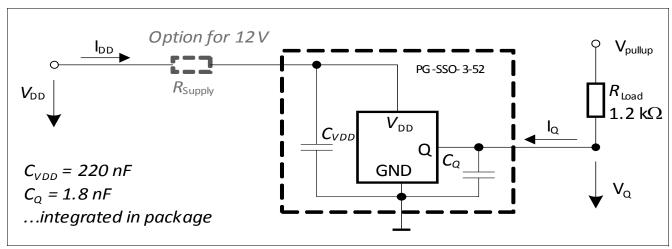
Table 1 Description

Туре	Marking	Ordering Code	Package
TLE4959C FX	59AIC1	SP001040492	PG-SSO-3-52



Description

The TLE4959C FX comes in a RoHs compliant three-pin package, qualified for automotive usage. It has two integrated capacitors on the lead frame (220 nF/1.8 nF). These capacitors increase the EMC robustness of the device. In 12 V applications it is further recommended to use a serial resistor R_{Supply} of 100 Ω (tbd) for protection on the supply line. A pull-up resistor R_{Load} is mandatory on the output pin and determines the maximum current flowing through the output transistor. A value of $1.2 \, k\Omega$ is recommended for the 5V application. (see Figure 1)



Typical Application Circuit Figure 1



Functional Description

1 **Functional Description**

The differential Hall sensor IC detects the motion of tooth and magnet encoder applications. To detect the motion of ferromagnetic objects, the magnetic field must be provided by a back biasing permanent magnet. Either south or north pole of the magnet can be attached to the rear unmarked side of the IC package (See Figure 2). The magnetic measurement is based on three equally spaced Hall elements, integrated on the IC. Both magnetic and mechanical offsets are cancelled by a self calibration algorithm.

Definition of the Magnetic Field Direction 1.1

The magnetic field of a permanent magnet exits from the north pole and enters the south pole. If a north pole is attached to the backside of the High End Transmission Sensor, the field at the sensor position is positive, as shown in Figure 2.

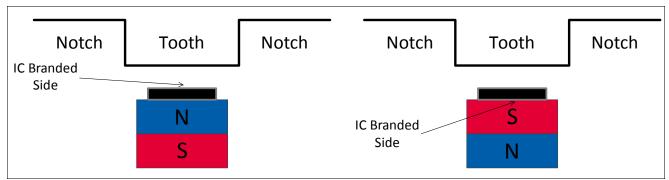


Figure 2 **Definition of the Positive Magnetic Field Direction**

1.2 **Block Diagram**

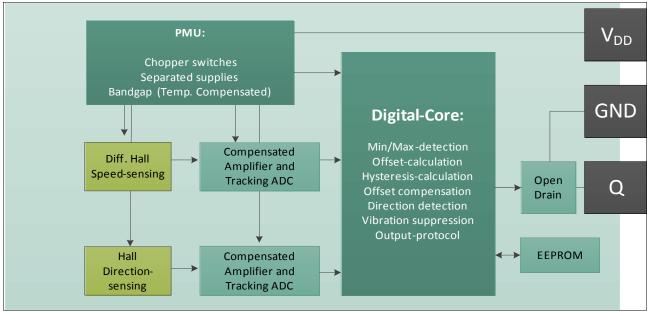


Figure 3 **Block Diagram**



Functional Description

1.3 Basic Operation

The speed signal calculated out of the differential hall elements, is amplified, filtered and digitized. An algorithm in the digital core for peak detection and offset calculation will be executed. The offset is fed back into the speed signal path with a digital to analog converter for offset correction. During uncalibrated mode, the output of the speed pulse is triggered in the digital core by exceeding a certain threshold of the tracking ADC. In calibrated mode the output is triggered by the visible hysteresis.

The direction signal is calculated out of center Hall signals. The direction signal is amplified, filtered, and digitized. In the digital core the direction and the vibration detection information is determined and the output protocol is issued.

1.4 Uncalibrated and Calibrated Mode

After power on the differential magnetic speed signal is tracked by an analog to digital converter (Tracking ADC) and monitored within the digital core. If the signal slope is identified as a rising edge or falling edge, the first output pulse is triggered. A second trigger pulse is issued with direction information.

In uncalibrated mode, the output protocols are triggered by the DNC (detection noise constant) in the speed path. After start up the sensor switches with the DNC min value and after that the DNC is adapted to the magnetic input signal amplitude.

The offset update starts if two valid extrema values are found and the direction of the update has the same orientation as the magnetic signal. For example, a positive offset update is being issued on a rising magnetic edge only. After a successful offset correction, the sensor is in calibrated mode. Switching occurs at the adaptive hysteresis threshold level.

In calibrated mode, the DNC is adapted to magnetic input signal amplitude with a minimum of ΔB_{limit} . The output pulses are then triggered with adaptive hysteresis.

1.5 Hysteresis Concept

The adaptive hysteresis is linked to the input signal. Therefore, the system is able to suppress switching if vibration or noise signals are smaller than the adaptive hysteresis levels. The minimum hysteresis level is ΔB_{limit} .

The visible hysteresis keeps the excellent performance in large pitch transmission application wheels.

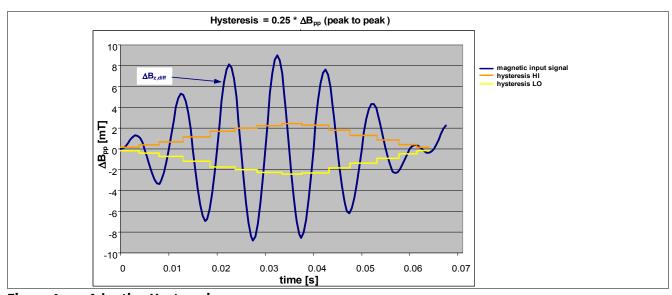


Figure 4 Adaptive Hysteresis



Functional Description

1.6 **Rotational Direction**

The direction signal is digitized by an analog to digital converter (direction ADC) and fed into the digital core. Depending upon the rotation direction of the target wheel, the signal of the center probe anticipates or lags behind for 90°. This phase relationship is evaluated and converted into rotation direction information by sampling the signal of the center probe in the proximity of the zero crossing of the "speed" bridge signal.

The first pulse after power (power on pulse) has a different length to signalize that there is no direction information available.

Forward pulse (t_{fwd}) is issue if the wheel rotates from pin 1 to pin 3

Backward pulse $(t_{\rm bwd})$ is issue if the wheel rotates from pin 3 to pin 1

Forward/backward pulse length could be inverted via EEPROM settings.

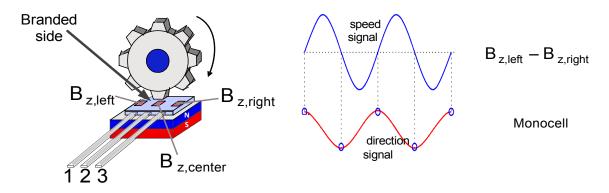


Figure 5 **Direction definition**

In case of high speed has been enable, the direction detection is switched off as soon as the frequency reach 4.3 kHz. To enter or leave the high frequency, two consecutive periods have to be larger or smaller than the frequency limit. this may delay the high frequency pulse at power on.

1.7 **Vibration Suppression**

The magnetic signal amplitude and the direction information are used for detection of parasitic magnetic signals. Unwanted magnetic signal can be caused by angular or air gap vibrations. If an input signal is identified as a vibration the output pulse will be suppressed.



General Characteristics

General Characteristics 2

Absolute Maximum Ratings 2.1

Absolute Maximum Ratings Table 2

Parameter	Symbol		Values	;	Unit	Note or Test Condition			
		Min.	Тур.	Max.					
Supply voltage without	V_{DD}	-16	-	18	V	continuous, T _J ≤ 175°C			
supply resistor				27	V	max. 60 s, T _J ≤ 175°C			
		-18			٧	max. 60 s, T _J ≤ 175°C			
Output OFF voltage	$V_{\rm Q_OFF}$	-1.0	-		V	max. 1 h, <i>T</i> _{Amb} ≤ 40°C			
		-0.3	-	26.5	V	continuous, T _J ≤ 175°C			
Output ON voltage	$V_{\rm Q_ON}$	_	-	16	٧	continuous, T _{Amb} ≤ 40°C			
		_	-	18	V	max. 1 h, T _{Amb} ≤ 40°C			
		_	-	26.5	V	max. 60 s, T _{Amb} ≤ 40°C			
Junction temperature range	T _J	-40	_	185	°C	exposure time: max. $10 \times 1 \text{ h}$, $V_{DD} = 16 \text{V}$			
Magnetic field induction	B _Z	-5	-	5	Т	magnetic pulse during magnet magnetization valid 10 s with $T_{\text{ambient}} \le 80^{\circ}\text{C}$			
ESD compliance	ESD _{HBM}	-6	_	6	kV	HBM ¹⁾			

¹⁾ ESD susceptibility, HBM according to EIA/JESD 22-A114B

Note:

Stresses above the max values listed here may cause permanent damage to the device. Exposure to absolute maximum rating conditions for extended periods may affect device reliability. Maximum ratings are absolute ratings; exceeding only one of these values may cause irreversible damage to the integrated circuit.



General Characteristics

Operating Range 2.2

All parameters specified in the following sections refer to these operating conditions unless otherwise specified.

General Operating Conditions Table 3

Parameter	Symbol		Value	S	Unit	Note or Test Condition		
		Min.	Тур.	Max.				
Supply voltage without supply resistance R _s	V_{DD}	4.0	-	16	V			
Continuous Output Off voltage	$V_{\mathrm{Q_OFF}}$	-	-	16	٧			
Supply voltage power- up/down voltage ramp	$dV_{\rm DD}/{\rm dt}$	3.0	_	1e4	V/ms			
Supply current	I_{DD}	8.0	_	13.4	mA			
Continuous output On current	$I_{\rm Q_ON}$		_	15	mA	ated voltage =50 V ¹⁾ apacitor type X8R, ated voltage =50 V ¹⁾ acreasing rotational requency ecreasing rotational requency		
Capacitance between IC supply & ground pins	C_{VDD}	198	220	242	nF	capacitor type X8R, rated voltage =50 V ¹⁾		
Output capacitance between IC output and ground pins	C_{Q}	1.62	1.8	1.98	nF	capacitor type X8R, rated voltage =50 V ¹⁾		
Magnetic signal frequency range	f	0	-	10	kHz			
Frequency range for direction detection (hystersis)once high	f_{Dir}	0	-	4.3	kHz	increasing rotational frequency		
speed has been selected		0	-	4	kHz	decreasing rotational frequency		
Maximum number of EEPROM programming cycles	N _{PROG}			100	n			
Dynamic range of the magnetic field of the differential speed channel	DR _{mag_field_s}	-120	-	120	mT			
Dynamic range of the magnetic field of the direction channel	DR _{mag_field_dir}	-60	_	60	mT			
Static range of the magnetic field of the outer Hall probes in back-bias configuration	SR _{mag_field_s}	0	_	550	mT			
Static range of the magnetic field of the center Hall probe	DR _{mag_field_dir}	-100	_	450	mT			
Allowed static difference between outer probes	SR _{mag_field_diff}	-30	-	30	mT			
Normal operating junction temperature	T _J	-40	-	175	°C	exposure time: max. 250 at $T_J = 175$ °C, $V_{DD} = 16$ V		
		_	_	185	°C	exposure time: max. 10×1 h at $T_J = 185^{\circ}$ C, $V_{DD} = 16$ V, additive to ot lifetime		



General Characteristics

Table 3 **General Operating Conditions** (cont'd)

Parameter	Symbol		Value	S	Unit	Note or Test Condition		
		Min.	Тур.	Max.				
Not operational lifetime	T _{no}	-40		150	°C	without sensor function. Exposure time max 500 h @ 150°C; increased time for lower temperatures according to Arrhenius- Model, additive to other lifetime		
Ambient temperature range for device features reading and programming	T_{RDPROG}	15	25	130	°C	during programming at customer		
Temperature compensation range of magnetic material	TC		-600		ppm	internal compensation of magnetic signal amplitude of speed signal		

¹⁾ Specified at room temperature, test condition at 25°C with 1V at 1kHz, temperature variation to be added

In the operating range the functions given in the functional description are fulfilled Note:



Electrical and Magnetic Characteristics

Electrical and Magnetic Characteristics 3

All values specified at constant amplitude and offset of input signal, over operating range, unless otherwise specified. Typical values correspond to $V_S = 5 \text{ V}$ and $T_{Amb.} = 25 ^{\circ}\text{C}$

Table 4 **Electrical and Magnetic Parameters**

Parameter	Symbol		Values	;	Unit	Note or Test Condition	
		Min.	Тур.	Max.			
Output saturation voltage	V_{Qsat}	0	-	500	mV	I _Q ≤ 15 mA	
Clamping voltage V _{DD} -Pin	$V_{\mathrm{DD_clamp}}$	42	-		V	leakage current through ESD diode < 0.5mA	
Clamping voltage V _Q -Pin	$V_{ m Qclamp}$	42		-	V	leakage current through ESD diode < 0.5mA	
Reset voltage	V _{DD_reset}	2.8		3.6	V		
Output leakage current	I _{Qleak}	0	0.1	10	μΑ	V _Q = 18 V	
Output current limit during short-circuit condition	I _{Qshort}	30	_	80	mA		
Junction temperature limit for output protection	T_{prot}	190	-	205	°C		
Power on time	t _{power_on}	0.8	0.9	1	ms	during this time the output is locked to high.	
Delay time between magnetic signal switching point and corresponding output signal falling edge switching event	$t_{ m delay}$	10	14	19	μs	falling edge	
Output fall time	t_{fall}	2.0	2.5	3.0	μs	$V_{Pullup} = 5 \text{ V}, R_{Pullup} = 1.2 \text{ k}\Omega \text{ (+/-}10\%), C_Q = 1.8 \text{ nF (+/-}15\%),}$ valid between 80% - 20%	
		3.2	4.5	5.8	μs	$V_{Pullup} = 5 \text{ V}, R_{Pullup} = 1.2 \text{ k}\Omega \text{ (+/-} 10\%), C_Q = 1.8 \text{ nF (+/-}15\%),}$ valid between 90% - 10%	
Output rise time	t _{rise} 1)	4	-	11.4	μs	$R_{\rm Pullup} = 1.2 \text{ k}\Omega \text{ (+/-10\%)},$ $C_{\rm Q} = 1.8 \text{ nF (+/-15\%)},$ valid between 10% - 90%	
Digital noise constant of speed channel during start up	DNC _{min}	1.22	1.5	1.78	mT		
Adaptive hysteresis threshold	HYS _{adaptive}	-	25	-	%	EEPROM "HYST_ADAPT"Option 0	
		-	12.5	-	%	EEPROM "HYST_ADAPT"Option 1	
Period Jitter, $f \le 8 \text{ kHz}^{2}$	Jit _{8kHz}	-1	_	1	%	1 sigma, ΔB _{pkpk} = 3mT	
Period Jitter, $8kHz \le f \le 10kHz^{2}$	Jit _{10kHz}	-1.1		1.1	%	1 sigma, ΔB _{pkpk} = 3mT	
Number of wrong pulses at	n _{Start}	-	-	0	n	in forward rotational direction	
start-up		0	-	1	n	in backward rotational direction	



Electrical and Magnetic Characteristics

Table 4 **Electrical and Magnetic Parameters** (cont'd)

Parameter	Symbol		Values	;	Unit	Note or Test Condition	
		Min.	Тур.	Max.			
Global run out ³⁾	Runout _{glob}	0	-	40	%	of magnetic speed signal amplitude	
		0	-	60	%	of magnetic speed signal amplitude with reduced performance on stand-still functionality	
	Runout _{glob}	0	-	40	%	of magnetic direction signal amplitude	
		0	-	60	%	Of magnetic direction signal amplitude with reduced performance on stand-still functionality	
Tooth to tooth run out (peak to peak variation on two	Runout _{tooth}	0	-	40	%	of magnetic speed signal amplitude	
consecutive teeth / pole-pair) ³⁾	Runout _{tooth}	0	-	40	%	of magnetic direction signal amplitude	

¹⁾ Value of capacitor: 1.8 nF±10%; ceramic: X8R; maximum voltage: 50 V

Note:

The listed Electrical and magnetic characteristics are ensured over the operating range of the integrated circuit. Typical characteristics specify mean values expected over the production spread. If not other specified, typical characteristics apply at T_{Amb} = 25°C and V_{S} = 5 V.

3.1 **Output protocols**

TLE4959C FX provides the option to select output protocol without direction detection. As well as the following direction detection options where the direction is provided via PWM protocol.

Table 5 Option 1

Parameter	Symbol		Values	•	Unit	Note or Test Condition	
		Min.	Тур.	Max.			
Output pulse in forward direction	t _{fwd}	38	45	52	μs		
Output pulse in backward direction	t _{bwd}	114	135	155	μs		
Power on pulse	t _{power-on}	153	180	207	μs		

²⁾ Parameter not subject to productive test. Verified by lab characterization based on jitter-measurement > 1000 periods

³⁾ Defined as 1-(amplitude_min/amplitude_max)



Electrical and Magnetic Characteristics

Option 1 (cont'd) Table 5

Parameter	Symbol		Values	;	Unit	Note or Test Condition
		Min.	Тур.	Max.		
Output pulse at High speed	t _{high_speed}	25.5	30	34.5	μs	pulse available after High speed option has been selected
Stand still pulse	t _{stand-still}	51	60	69	μs	pulse available stand still after pulse option has been selected. Pulse delivered if no relevant magnetic signal change has been detected within 50ms

Note:

 V_{Pullup} = 5 V, RPullup = 1.2 k Ω (+/-10%), CQ = 1.8 nF (+/-15%), valid between 50% of falling edge to

50% of next rising edge

Option 2 Table 6

Parameter	Symbol		Values	;	Unit	Note or Test Condition		
		Min.	Тур.	Max.				
Output pulse in forward direction	t_{fwd}	38	45	52	μs			
Output pulse in backward direction	t _{bwd}	153	180	207	μs			
Output pulse at High speed	t _{high_speed}	38	45	52	μs	pulse available after High speed option has been selected		

Attention: First pulse after magnetic edge suppressed

 $V_{Pullup} = 5 \text{ V}$, $RPullup = 1.2 \text{ k}\Omega$ (+/-10%), CQ = 1.8 nF (+/-15%), valid between 50% of falling edge to Note:

50% of next rising edge

Option 3 Table 7

Parameter	Symbol		Values	,	Unit	Note or Test Condition		
		Min.	Тур.	Max.				
Output pulse in forward direction	t _{fwd}	51	60	69	μs			
Output pulse in backward direction	t _{bwd}	102	120	138	μs			
Power on pulse	t _{power-on}	25.5	30	34.5	μs			
Output pulse at High speed	$t_{ m high_speed}$	25.5	30	34.5	μs	pulse available after High speed option has been selected		



Electrical and Magnetic Characteristics

 V_{Pullup} = 5 V, RPullup = 1.2 k Ω (+/-10%), CQ = 1.8 nF (+/-15%), valid between 50% of falling edge to Note:

50% of next rising edge

Table 8 Option 4

Parameter	Symbol		Values	i	Unit	Note or Test Condition		
		Min.	Тур.	Max.				
Output pulse in forward direction	t_{fwd}	38	45	52	μs			
Output pulse in backward direction	t _{bwd}	76.5	90	103.5	μs			
Power on pulse	t _{power-on}	153	180	207	μs			
Output pulse at High speed	t _{high_speed}	38	45	52	μs	pulse available after High speed option has been selected		

 V_{Pullup} = 5 V, RPullup = 1.2 k Ω (+/-10%), CQ = 1.8 nF (+/-15%), valid between 50% of falling edge to Note:

50% of next rising edge



EEPROM Functional Description

EEPROM Functional Description 4

4.1 **Serial Interface**

The serial interface is used to set parameter and to program the sensor IC, it allows writing and reading of internal registers. Data transmission to the IC is done by supply voltage modulation, by providing the clock timing and data information via only one line. Data from the IC are delivered via the output line, triggered by as well clocking the supply line. In normal application operation the interface is not active, for entering that mode a certain command right after power-on is required.

A detailed document (TLE4959C FX EEPROM Programming Guide) is available on request. It contains the description of electrical timing and voltage requirements, as well as the information about data protocol, available registers and addresses.

4.1.1 **Data Transmission**

Commands to the sensor are sent by modulating the supply voltage between two levels $V_{\rm DD,high}$ and $V_{\rm DD,low}$. They are sent in series of 17 pulses corresponding to 16 bit words, with MSB transmitted first and LSB last, respectively the stop bit. Each of the 16 pulses is coded by the duty cycle as logical "0" or "1". Logical "1" is represented by a duty cycle of 2/3 of the period on $V_{\rm DD,high}$, logical "0" is represented by a duty cycle of 1/3 at $V_{\rm DD,high}$. This forms the bit information and acts also as serial interface clock. Data transmission from the device is represented by the state of the output, high for logical "1" and low for logical "0". Recommended period length is around 200 (tbd) µs per bit.

End of word is indicated by a long "low" supply (> 750 ms, first 30 ms should be > $V_{\rm DD,high}$, remaining time $< V_{\rm DD\ low}$). Please note, that for transmission of 16 data bits in total 17 pulses on $V_{\rm DD}$ are necessary. If more than 16 input bits are transmitted the output bits are irrelevant (transmission buffer empty), whereas the input bits remain valid and start overwriting the previously transmitted bits. In any case the last 17 transmitted bits are interpreted as transmitted data word (16 bit) + 1 stop bit.

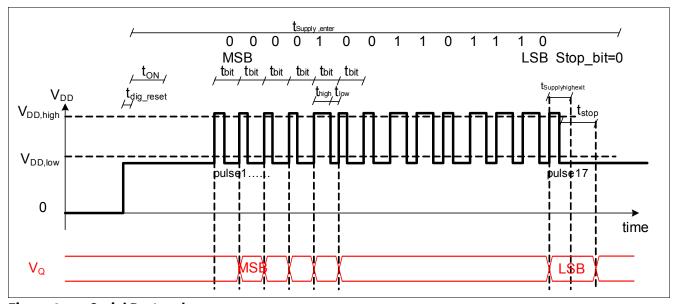


Figure 6 **Serial Protocol**



EEPROM Functional Description

EEPROM Description 4.2

Several options of TLE4959C FX can be programmed via an EEPROM to optimize the sensor algorithm to the individual target wheel and application requirements. The EEPROM memory is organized in 2 customer lines. Each line is composed of 16 data bits and additional 6 bits for error detection and correction, based on ECC (Error Correction Code). For more detailed information about EEPROM access and programming an additional document is available on request.

Table	9 EEPROM Address 0x0														
15	14	13	12	11	10	9	8	7	6	5	4	3	2	1	0
					•				•	•					

Table 10 Functional Description Address 0x0					
Field	Bit	Туре	Description	TLE4959C FX	
Not used	15	r	Always read as "0"	0	
Not used	14	rw	To be set to "0"	0	
HIGH_SPEED	13	rw	0 = Enabled motion detection 1 = According selected protocol when above 4.3kHz	0	
Not used	12	rw	To be set to "0"	0	
STAND_EN	11	rw	0=disable stand-still pulse 1=enable stand-still pulse Stand still pulse is provided, if enabled, only if PW_CHIOICE=00	0	
Not used	100	rw	To be set to "0000000000"	0000000000	

Table	11	EEPROM Address 0x1													
15	14	13	12	11	10	9	8	7	6	5	4	3	2	1	0

Table 12	F	Description	Adduses 0.41
Table 12	Functional	Description	Address 0x1

Field	Bit	Туре	Description	TLE4959C FX
Not used	15:14	rw	To be set to "01"	01
PW_CHOICE	13:12	rw	Choice of PWM protocol for direction detection. 00 = Option 1 01 = Option 2 10 = Option 3 11 = Option 4	11
FORWARD_DEF	11	rw	0 = None invertion of forward definition 1 = Invertion of forward definition	0
EDGE_POLAR	10	rw	0 = None invertion 1 = Invertion	0
HYST_ADAPT	9	rw	0 = 25% 1 = 12.5%	1



EEPROM Functional Description

Table 12 **Functional Description Address 0x1** (cont'd)

Field	Field Bit Type Description		TLE4959C FX	
Not used	8 5	rw	To be set to "1101"	1101
DNC_ADAPT	4	rw	DNC Adaption: 0 = 25% 1 = 12.5%	0
Not used	3	rw	To be set to "0"	0
DIR_ENABLE	2	rw	0 = Direction detection off 1 = Direction detection on	1
Not used	1	rw	To be set to "1"	1
LOCK	0	rw	0 = User area of EEPROM is unlocked 1 = User area of EEPROM is locked (no reprogramming possible)	0



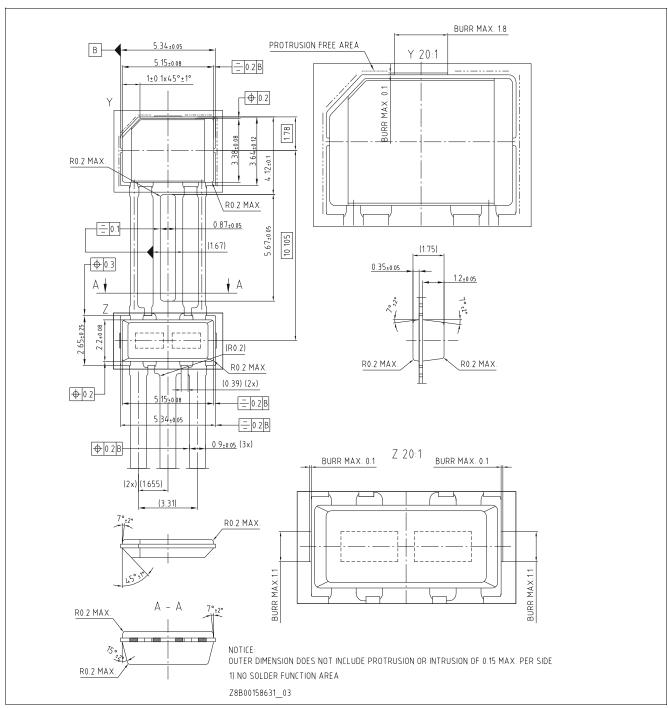
Package Information

5 **Package Information**

Pure tin covering (green lead plating) is used. The product is RoHS (Restriction of Hazardous Substances) compliant and marked with letter G in front of the data code marking and may contain a data matrix code on the rear side of the package (see also information note 136/03). Please refer to your key account team or regional sales if you need further information.

The specification for soldering and welding is defined in the latest revision of application note "Recommendation for Board Assembly-Hallsensor SSO Packages".

5.1 **Package Outline**



PG-SSO-3-52 (Plastic Green Single Slim Outline), Package Dimensions Figure 7



Package Information

Position of the Hall Element 5.2

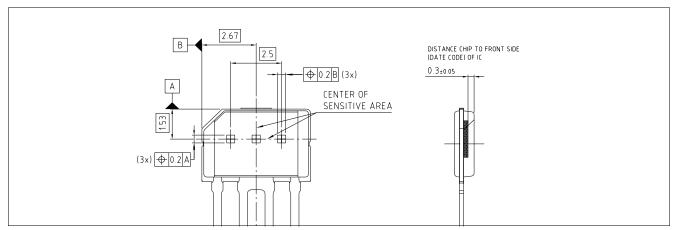


Figure 8 Position of the Hall Elements in PG-SSO-3-52 and Distance to the Branded Side

Marking and Data Matrix Code 5.3

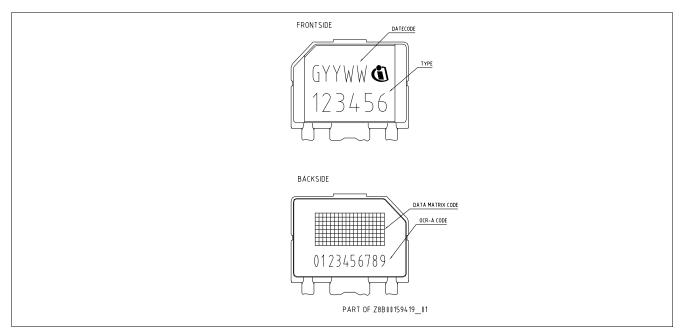


Figure 9 Marking of PG-SSO-3-52 Package

Pin Configuration and Sensitive Area 5.4

Table 13 **Pin Description**

Pin Number ¹⁾	Symbol	Function
1	V_{DD}	Supply Voltage
2	GND	Ground
3	Q	Open Drain Output

¹⁾ Refer to frontside view: leftmost pin corresponding to pin number 1



Package Information

Packing Information 5.5

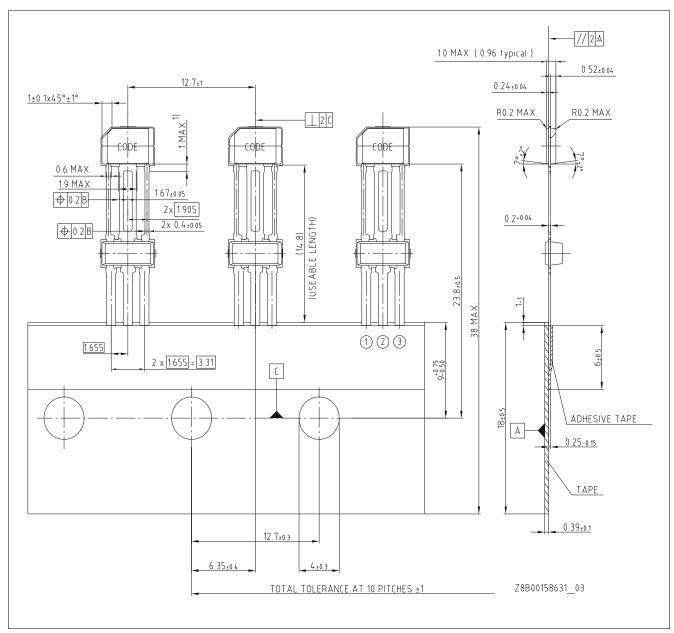


Figure 10 PG-SSO-3-52 Ammopack



Revision History

Revision History 6

Revision	Date	Changes
1.0	2017-10-05	First version of released datasheet

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